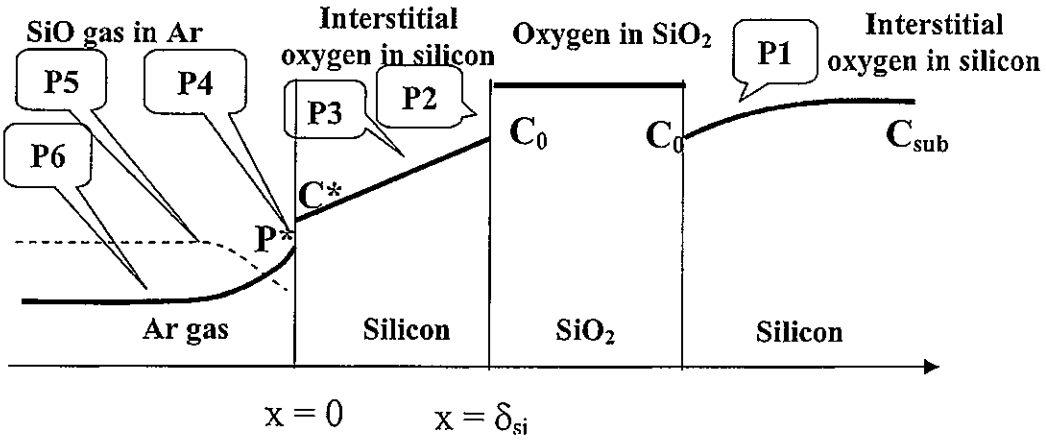


Figure 1

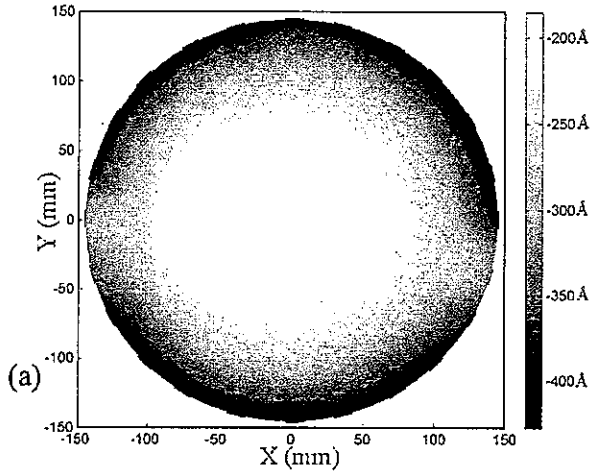


Figure 2a

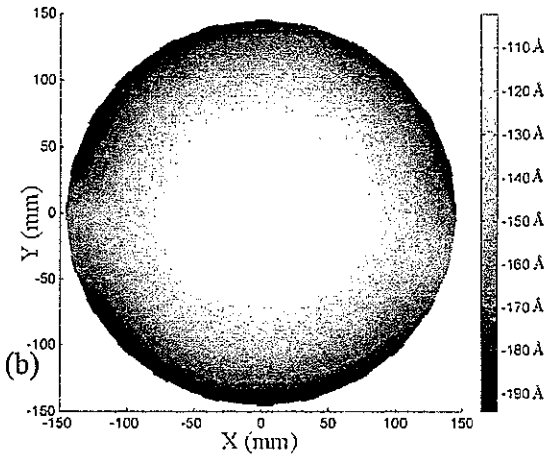


Figure 2b

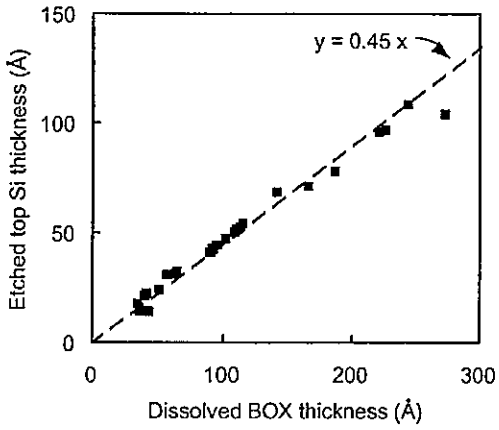


Figure 3

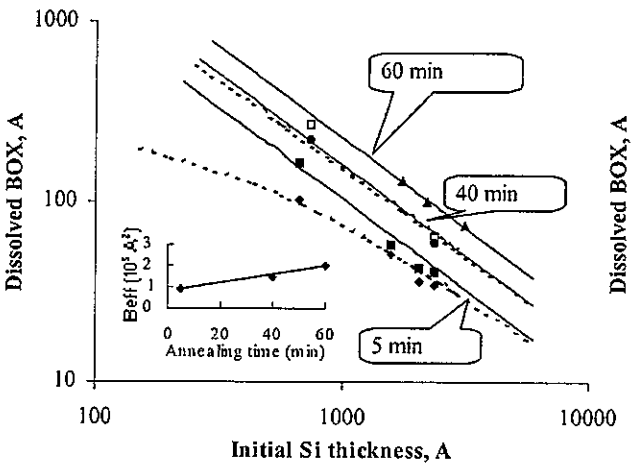


Figure 4

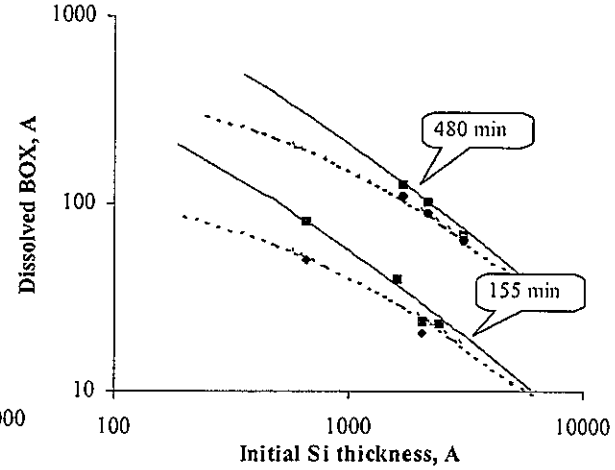


Figure 5

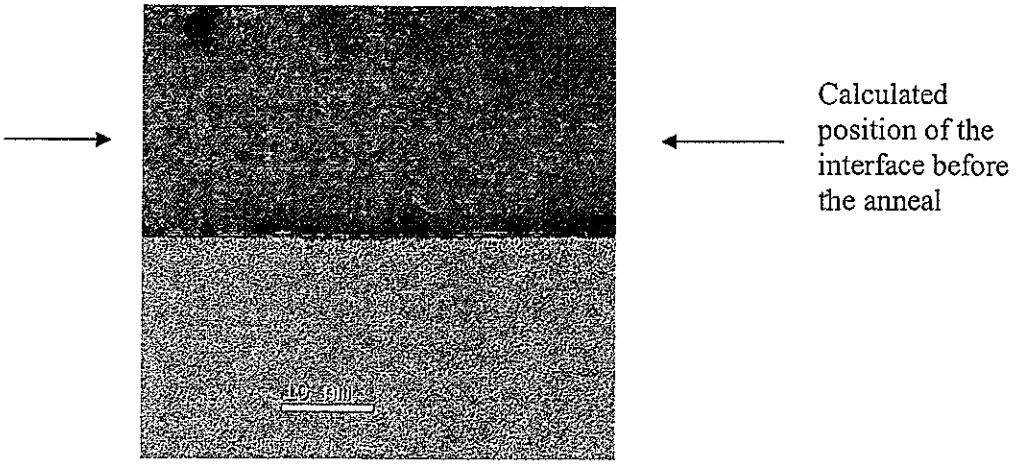


Figure 6

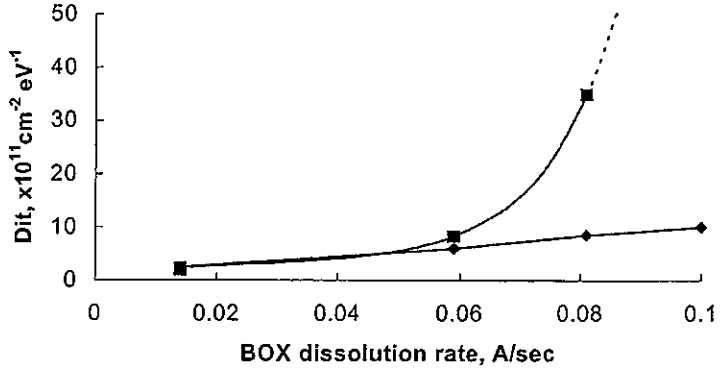


Figure 7

Temperature [°C]	B exp [cm^2/sec]	B theo (Eq.11) [cm^2/sec]	A center [Å]	A edge [Å]
1200	$3.24x10^{-15}$	$3.25x10^{-15}$	30	0
1150	$7.87x10^{-16}$	$1.06x10^{-15}$	1070	236

Figure 8

Top Si thickness after anneal [Å]	Anneal time [min]	Max rate of BOX dissolution [Å/sec]	Dit $x10^{11}$ [cm^{-2} eV^{-1}]	Dit control $x10^{11}$ [cm^{-2} eV^{-1}]	μe [cm^2/Vs]	μe control [cm^2/Vs]	μh [cm^2/Vs]	μh control [cm^2/Vs]
2300	5	0.01	2	2.5	692	750	202	200
2250	40	0.01	2.4	2.5	661	750	195	200
550	40	0.06	8.3	6	414	520	116	140
400	60	0.08	35	8.5	170	400	55	110
310	6	0.1	-	10	-	350	-	90

Figure 9